

AFGHL75T65SQDC

THERMAL CHARACTERISTICS

Rating	Symbol	Max	Unit
Thermal resistance junction-to-case, for IGBT	$R_{\theta JC}$	0.4	°C/W
Thermal resistance junction-to-case, for Diode	$R_{\theta JC}$	1.55	°C/W
Thermal resistance junction-to-ambient	$R_{\theta JA}$	40	°C/W

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Collector-emitter breakdown voltage, gate-emitter short-circuited	$V_{GE} = 0\text{ V},$ $I_C = 1\text{ mA}$	BV_{CES}	650	–	–	V
Temperature Coefficient of Breakdown Voltage	$V_{GE} = 0\text{ V},$ $I_C = 1\text{ mA}$	$\frac{\Delta BV_{CES}}{\Delta T_J}$	–	0.6	–	V/°C
Collector-emitter cut-off current, gate-emitter short-circuited	$V_{GE} = 0\text{ V},$ $V_{CE} = 650\text{ V}$	I_{CES}	–	–	250	μA
Gate leakage current, collector-emitter short-circuited	$V_{GE} = 20\text{ V},$ $V_{CE} = 0\text{ V}$	I_{GES}	–	–	±400	nA

ON CHARACTERISTICS

Gate-emitter threshold voltage	$V_{GE} = V_{CE}, I_C = 75\text{ mA}$	$V_{GE(th)}$	3.4	4.9	6.4	V
Collector-emitter saturation voltage	$V_{GE} = 15\text{ V}, I_C = 75\text{ A}$ $V_{GE} = 15\text{ V}, I_C = 75\text{ A}, T_J = 175^\circ\text{C}$	$V_{CE(sat)}$	–	1.6	2.1	V
			–	2.0	–	

DYNAMIC CHARACTERISTICS

Input capacitance	$V_{CE} = 30\text{ V},$ $V_{GE} = 0\text{ V},$ $f = 1\text{ MHz}$	C 0 6.5 38 6.5tf8efBT8 0 0 or
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ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
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TYPICAL CHARACTERISTICS

Figure 7. Saturation Voltage vs. Case

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TYPICAL CHARACTERISTICS

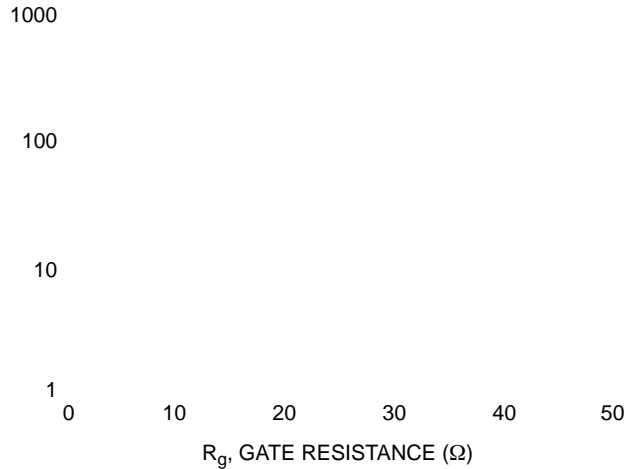


Figure 13. Turn-On Characteristics vs. Gate Resistance

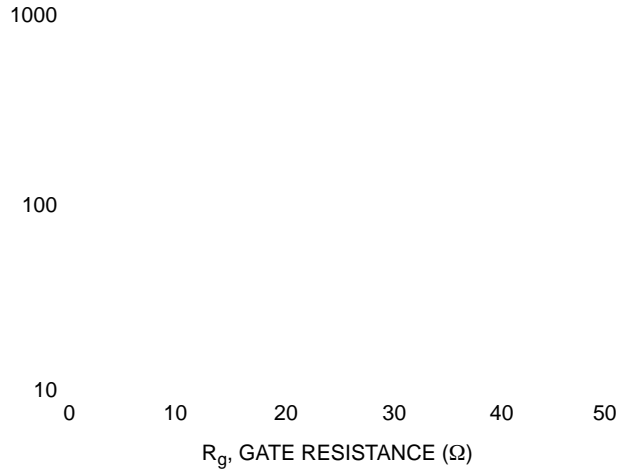


Figure 14. Turn-Off Characteristics vs. Gate Resistance

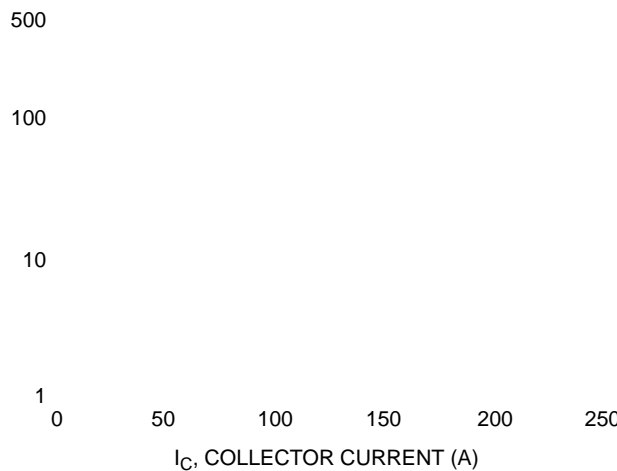


Figure 15. Turn-On Characteristics vs. Collector Current

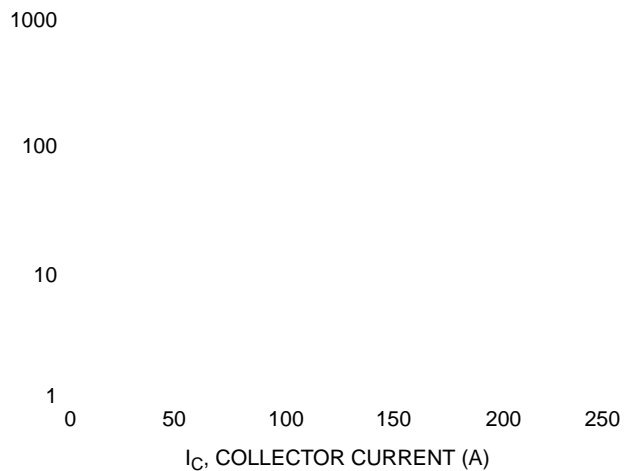


Figure 16. Turn-Off Characteristics vs. Collector Current

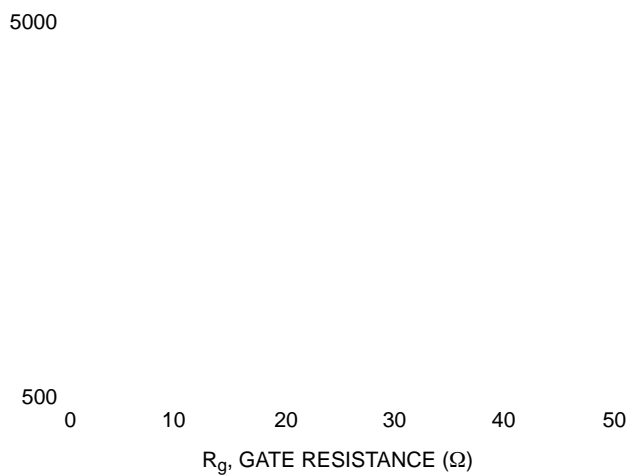


Figure 17. Switching Loss vs. Gate Resistance



Figure 18. Switching Loss vs. Collector Current

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